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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/939,253	08/24/2001	James M. Derderian	4830US (01-0106)	2189
24247	7590	08/25/2004	EXAMINER	
TRASK BRITT P.O. BOX 2550 SALT LAKE CITY, UT 84110			WILLIAMS, ALEXANDER O	
			ART UNIT	PAPER NUMBER
			2826	

DATE MAILED: 08/25/2004

Please find below and/or attached an Office communication concerning this application or proceeding.

Office Action Summary

Application No.

09/939,253

Applicant(s)

DERDERIAN, JAMES M.

Examiner

Alexander O Williams

Art Unit

2826

-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --
Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133). Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

Status

- 1) ☐ Responsive to communication(s) filed on 06 August 2004.
- 2a) ☐ This action is FINAL. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

Disposition of Claims

- 4) ☒ Claim(s) 1-39 and 41-67 is/are pending in the application.
- 4a) Of the above claim(s) 14-16, 27-30, 34-36, 41 and 48-67 is/are withdrawn from consideration.
- 5) ☐ Claim(s) _____ is/are allowed.
- 6) ☒ Claim(s) 1-13, 17-26, 31-33, 37-39 and 42-44 is/are rejected.
- 7) ☐ Claim(s) _____ is/are objected to.
- 8) ☐ Claim(s) _____ are subject to restriction and/or election requirement.

Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☐ The drawing(s) filed on _____ is/are: a) ☐ accepted or b) ☐ objected to by the Examiner.
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
Replacement drawing sheet(s) including the correction is required if the drawing(s) is objected to. See 37 CFR 1.121(d).
- 11) ☐ The oath or declaration is objected to by the Examiner. Note the attached Office Action or form PTO-152.

Priority under 35 U.S.C. § 119

- 12) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some * c) ☐ None of:
- ☐ Certified copies of the priority documents have been received.
 - ☐ Certified copies of the priority documents have been received in Application No. _____.
 - ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).

* See the attached detailed Office action for a list of the certified copies not received.

Attachment(s)

- | | |
|--|---|
| 1) <input type="checkbox"/> Notice of References Cited (PTO-892) | 4) <input type="checkbox"/> Interview Summary (PTO-413)
Paper No(s)/Mail Date. _____ |
| 2) <input type="checkbox"/> Notice of Draftsperson's Patent Drawing Review (PTO-948) | 5) <input type="checkbox"/> Notice of Informal Patent Application (PTO-152) |
| 3) <input type="checkbox"/> Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08)
Paper No(s)/Mail Date _____ | 6) <input type="checkbox"/> Other: _____ |

Art Unit: 2826

Serial Number: 09/939253 Attorney's Docket #: 4830US(01-0106)
Filing Date: 8/24/01;

Applicant: Derderian

Examiner: Alexander Williams

Applicant's RCE filed 8/6/04 has been acknowledged.

Applicant's Amendment filed 7/16/04 have been acknowledged. The claims being examined are claims 1 to 13, 17-26, 31 to 33, 37 to 39 and 42 to 44.

This application contains claims 14 to 16, 27 to 30, 34 to 36, 41 and 48 to 67 drawn to an invention non-elected without traverse in Paper No. 11.

Claims 40 and 68 to 102 have been canceled.

Note: Initially, this application had two restriction requirement in which the species 7, figure 10 and claims that read on this species. Upon the beginning of the examination of this application, the Examiner still is examining claims directed to this species. Before, art can be continued to be applied or the amendment can be understood to read over the outstanding rejection, the Examiner would like to better understand Applicant's amended claims language.

Claims 1 to 13, 17 to 26, 31 to 33, 37 to 39 and 42 to 44 are rejected under 35 U.S.C. § 112, second paragraph, as being indefinite for failing to particularly point out and distinctly claim the subject matter which applicant regards as the invention.

In claim 1, it is unclear and confusing to what is meant by "the dielectric spacer layer protruding from the surface substantially the predetermined distance before the semiconductor die is positioned adjacent to the adjacent semiconductor." Should this be --semiconductor die--? How is the nonconfluent spacer layer protruding from the surface? Is it within the semiconductor device?

In claim 19, it is unclear and confusing to what is meant and how "prior to securing an intermediate conductive element to any of the bond pads, protruding

Art Unit: 2826

from the active surface substantially a predetermined distance the active surface of the first semiconductor device is to be spaced apart from the back side of a second semiconductor device upon positioning the second semiconductor device over the first semiconductor device so as to accommodate the intermediate conductive elements.” The Examiner is interested in finding the final structure claimed by Applicant. The before and after language is given little weight in examining the claimed structure. The use of “is to be” in the claim language does not recite positive structure to the claim as actually a part of the structure of the claim. How is the nonconfluent spacer layer protruding from the active surface? Is it within the semiconductor device?

Any of claims 1 to 13, 17 to 26, 31 to 33, 37 to 39 and 42 to 44 not specifically addressed above are rejected as being dependent on one or more of the claims which have been specifically objected to above.

The following is a quotation of the appropriate paragraphs of 35 U.S.C. § 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been

Art Unit: 2826

obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

Note: The art is not applied to amended claim in this action. Applicant's arguments are misplaced to figure 6 and not to the Examiner details of figure 8. Also, Applicant's arguments show reference to the arguments that makes confusion to understanding arguments relating to these claims.

Claims 1 to 10, 17, 19 to 26, 33 and 42 to 44 are rejected under 35 U.S.C. § 102(e) as being anticipated by Foster (U.S. Patent # 6,552,416 B1).

For example, in claim 1, Foster (figures 1 to 10c) specifically figure 8 show a semiconductor device for use in a stacked multi-chip assembly, comprising: a semiconductor die **31**; and a dielectric spacer layer **32** formed on and secured to (by 20 and lower 33) at least a portion of a surface of said semiconductor die (by 20 and lower 33) and protruding from the surface substantially a predetermined distance that said semiconductor die and an adjacent semiconductor die **30** of said stacked multi-chip assembly are to be spaced apart from one another, said spacer layer including voids **(in figure 8, middle portion between the two stacks of 33 and 20s)** communicating with a lateral periphery thereof.

For example, in claim 19, Foster (figures 1 to 10c) specifically figure 8 show a semiconductor device assembly, comprising: a first semiconductor device **31**; a nonconfluent spacer layer **32** comprising dielectric material secured to a surface of said first semiconductor device, a second semiconductor device **30** positioned over said first semiconductor device, a surface of said second semiconductor device being secured to said nonconfluent spacer layer.

Claims 1 to 10, 13, 17, 19 to 26, 32, 33, 37 to 39 and 42 to 44 are rejected under 35 U.S.C. § 102(e) as being anticipated by Shim et al. (U.S. Patent # 6,531,784 B1).

For example, in claim 1, Shim et al. (figures 1 to 11) specifically figure 8 show a semiconductor device for use in a stacked multi-chip assembly, comprising: a semiconductor die **14**; and a dielectric spacer layer **50A,50C** formed and secured to on at least a portion of a surface of said semiconductor die and protruding from the surface substantially a predetermined distance that said semiconductor die and an adjacent semiconductor die **16** of said stacked

multi-chip assembly are to be spaced apart from one another, said spacer layer including voids (**in figure 8, middle portion between the two 50A,50Cs**) communicating with a lateral periphery thereof.

For example, in claim 19, Shim et al. (figures 1 to 11) specifically figure 8 show a semiconductor device assembly, comprising: a first semiconductor device **14**; a nonconfluent spacer layer **50A,50C** comprising dielectric material secured to on a surface of said first semiconductor device, a second semiconductor device **16** positioned over said first semiconductor device, a surface of said second semiconductor device being secured to said nonconfluent spacer layer.

In claim 37, Shim et al. (figures 1 to 11) specifically figure 8 show a substrate **12** upon which one of said first semiconductor device **14** and said second semiconductor device **16** is positioned.

In claim 38, Shim et al. (figures 1 to 11) specifically figure 8 show at least one bond pad (**inherit in figure 8, shown as 58 in figure 9**) of at least one of said first semiconductor device and said second semiconductor device **31** is in communication (**through 28B**) with a corresponding contact area **22** of said substrate **12**.

In claim 39, Shim et al. (figures 1 to 11) specifically figure 8 show the substrate comprising at least one of a circuit board **12**, an interposer, another semiconductor device, and leads.

Claims 11 and 12 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shim et al. (U.S. Patent # 6,531,784 B1) in view of Smith, Jr. et al. (U.S. Patent # 6,049,370).

Shimi et al. show the features of the claimed invention as detailed above, but fail to explicitly show a spacer layer comprising polymer, where as the polymer comprises a photoimageable polymer. Shimi does disclose that the jumper strips 50A, 50B, and 50C can be made of a variety of insulative materials and by a variety of techniques. For example, they can be fabricated from a resin tape or a sheet of fiberglass impregnated with an epoxy resin using conventional circuit

Art Unit: 2826

tape or PCB fabrication techniques. Photoimageable polymer is defined to be a photoresist polymer.

Smith, Jr. et al. is cited for showing liquid crystal light valve using internal, fixed spacers. Specifically, Smith, Jr. et al. (figures 2 to 5) specifically figure 3 discloses a variety of materials may be used to form the spacer pads 40, including an oxide, such as silica or indium tin oxide, a metal, such as chromium, aluminum, or gold, and polymers, such as polyimides or photoresist materials for the purpose of giving spacing between electrical connecting materials.

Therefore, it would have been obvious to one of ordinary skill in the art to use Smith, Jr. et al.'s photoresist polymer spacer to modify Shim et al.'s spacers for the purpose of giving spacing between electrical connecting materials.

Claims 18 and 31 are rejected under 35 U.S.C. 103(a) as being unpatentable over Shim et al. (U.S. Patent # 6,531,784 B1) in view of Blanton (U.S. Patent # 5,220,200).

Initially, it is noted that the 35 U.S.C. § 103 rejection based on a dielectric spacer layer and a plurality of at least partially superimposed, contiguous, adhered sublayers deals with an issue (i.e., the integration of multiple pieces into one piece or conversely, using multiple pieces in replacing a single piece) that has been previously decided by the courts.

In Howard v. Detroit Stove Works 150 U.S. 164 (1893), the Court held, "it involves no invention to cast in one piece an article which has formerly been cast in two pieces and put together...."

In In re Larson 144 USPQ 347 (CCPA 1965), the term "integral" did not define over a multi-piece structure secured as a single unit. More importantly, the court went further and stated, "we are inclined to agree with the solicitor that the use of a one-piece construction instead of the [multi-piece] structure disclosed in Tuttle et al. would be merely a matter of obvious engineering choice" (bracketed material added). The court cited In re Fridolph for support.

In re Fridolph 135 USPQ 319 (CCPA 1962) deals with submitted affidavits relating to this issue. The underlying issue in In re Fridolph was related to the end result of making a multi-piece structure into a one-piece structure. Generally, favorable patentable weight was accorded if the one-piece structure yielded results not expected from the modification of the two-piece structure into a single piece structure.
Shim et al. dielectric layer can be a plurality of at least partially superimposed, contiguous, adhered sublayers.

Blanton is cited for showing provision of substrate pillars to maintain chip standoff. Specifically, Blanton (figures 1 to 3) specifically figure 3 discloses dielectric layer can be a plurality of at least partially superimposed, contiguous, adhered sublayers for the purpose of providing standoff means to space an integrated circuit.

Therefore, it would have been obvious to one of ordinary skill in the art to use the dielectric spacer layer and a plurality of at least partially superimposed, contiguous, adhered sublayers as "merely a matter of obvious engineering choice" as set forth in the above case law. However, it would have been obvious to one of ordinary skill

Art Unit: 2826

in the art to use Blanton's series of layer to make a spacer to modify Shim et al.'s spacers for the purpose of providing standoff means to space an integrated circuit.

Claims 11, 13 and 32 are rejected under 35 U.S.C. 103(a) as being unpatentable over Foster (U.S. Patent # 6,552,416 B1) in view of Mueller et al. (U.S. Patent # 6,316,786 B1).

Foster show the features of the claimed invention as detailed above, but fail to explicitly show a spacer layer comprising (all types) at least one of a glass, a silicon oxide, a silicon nitride, and a silicon oxynitride.

Mueller et al. is cited for showing an organic opto-electronic devices. Specifically, Mueller et al. (figures 1A to 3c) specifically figure 1B discloses spacers 13 and 15 comprising silicon nitride, SiN.sub.x, SiO.sub.x, SiO.sub.2, Siliconoxynitride (SiON), organic compounds such as polyimides, aluminiumoxide, aluminiumnitride, or titaniumoxide, for example for the purpose of providing sufficient contact between the layers and damage between the layers are avoided.

Therefore, it would have been obvious to one of ordinary skill in the art to use Mueller et al.'s spacer to modify Foster's spacers for the purpose of providing sufficient contact between the layers and damage between the layers are avoided.

Response

Applicant's arguments filed 8/6/04 have been fully considered, but are not understand in view of the outstanding grounds of rejections detailed above. New rejections are applied to the new claims.

Art Unit: 2826

Field of Search	Date
U.S. Class and subclass: 257/686,685,777,778,784-787,734,737,738,723,730,773	9/9/02 2/22/03 5/8/03 8/18/03 11/17/03 5/4/04
Other Documentation: foreign patents and literature in 257//686,685,777,778,784-787,734,737,738,723,730,773	9/9/02 2/22/03 5/8/03 8/18/03 11/17/03 5/4/04
Electronic data base(s): U.S. Patents EAST	9/9/02 2/22/03 5/8/03 8/18/03 11/17/03 5/4/04

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Alexander O Williams whose telephone number is (571) 272 1924. The examiner can normally be reached on M-F 6:30-7:00PM.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Nathan Flynn can be reached on (571) 272 1915. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

Art Unit: 2826

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see <http://pair-direct.uspto.gov>. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

AOW
5/4/04

A handwritten signature in black ink, appearing to read 'Alexander Williams', written in a cursive style.

Alexander Williams
Primary Examiner